WHAT IS CLAIMED IS:

1. A method for forming a film, comprising:

placing a substrate on a carrying base;

performing a first pre-sputtering using a target;

performing a second pre-sputtering using the target after the first pre-sputtering, wherein: while performing the first pre-sputtering and the second pre-sputtering, a shielding plate is positioned between the target and the substrate, and the first pre-sputtering and the second pre-sputtering have different process parameters;

moving the shielding plate away after the second pre-sputtering; and

performing a main sputtering on the substrate using the target to form a film on the substrate;

wherein no power is applied to the target after the second pre-sputtering and before the main sputtering.

2. The method according to claim 1, wherein: a gas introduced during the first pre-sputtering is different from a gas introduced during the second pre-sputtering.

3. The method according to claim 1, wherein: a gas introduced during the second pre-sputtering is the same as a gas introduced during the main sputtering.

4. The method according to claim 1, wherein: sputtering power applied to the target during the first pre-sputtering is different from sputtering power applied to the target during the second pre-sputtering.

5. The method according to claim 4, wherein: the sputtering power applied to the target during the second pre-sputtering is smaller than the sputtering power applied to the target during the first pre-sputtering.

6. The method according to claim 4, wherein: the sputtering power applied to the

target during the first pre-sputtering is equal to sputtering power applied to the target during the main sputtering.

7. The method according to claim 1, wherein: no power is applied to the target after the first pre-sputtering and before the second pre-sputtering.

8. The method according to claim 1, further comprising:

performing the main sputtering after the substrate is moved to a process position; and

applying power to the target to perform the main sputtering, wherein: no power is applied to the target after the second pre-sputtering is performed and before the substrate is moved to the process position.

9. A method for forming an aluminum nitride film, comprising:

placing a substrate on a carrying base;

performing a first pre-sputtering using a target containing aluminum;

performing a second pre-sputtering using the target containing aluminum after the first pre-sputtering, wherein: while performing the first pre-sputtering and the second pre-sputtering, a shielding plate is positioned between the target containing aluminum and the substrate, and the first pre-sputtering and the second pre-sputtering have different process parameters;

moving the shielding plate away after the second pre-sputtering; and

performing a main sputtering on the substrate using the target containing aluminum to form an aluminum nitride film on the substrate;

wherein no power is applied to the target containing aluminum after the second pre-sputtering and before the main sputtering.

10. The method according to claim 9, characterized in that, a gas introduced during the first pre-sputtering is different from a gas introduced during the second pre-

sputtering.

11. The method according to claim 9, wherein: a gas introduced during the first pre-sputtering includes a gas containing nitrogen and an inert gas.

12. The method according to claim 9, wherein: a gas introduced during the second pre-sputtering includes a gas containing nitrogen, a gas containing oxygen and an inert gas.

13. The method according to claim 9, characterized in that, a gas introduced during the second pre-sputtering is the same as a gas introduced during the main sputtering.

14. The method according to claim 9, wherein: sputtering power applied to the target containing aluminum during the first pre-sputtering is different from sputtering power applied to the target containing aluminum during the second pre-sputtering.

15. The method according to claim 14, wherein: the sputtering power applied to the target containing aluminum during the second pre-sputtering is smaller than the sputtering power applied to the target containing aluminum during the first pre-sputtering.

16. The method according to claim 14, wherein: the sputtering power applied to the target containing aluminum during the first pre-sputtering is equal to sputtering power applied to the target containing aluminum during the main sputtering.

17. The method according to claim 14, wherein: the sputtering power applied to the target containing aluminum during the first pre-sputtering is between 2500 watts and 4000 watts.

18. The method according to claim 14, wherein: the sputtering power applied to the target containing aluminum during the second pre-sputtering is between 200 watts and 4000 watts.

19. The method according to claim 9, wherein: no power is applied to the target containing aluminum after the first pre-sputtering and before the second pre-sputtering.

20. The method according to claim 9, further comprising:

performing the main sputtering after the substrate is moved to a process position; and

applying power to the target containing aluminum to perform the main sputtering, wherein no power is applied to the target containing aluminum after the second pre-sputtering is performed and before the substrate is moved to the process position.